

BFP540

NPN wideband transistor

Rev. 04 — 25 September 2007

Product data sheet

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NXP Semiconductors

NPN wideband transistor

BFQ540

FEATURES

- High gain
- High output voltage
- Low noise
- Gold metallization ensures excellent reliability
- Low thermal resistance.

APPLICATIONS

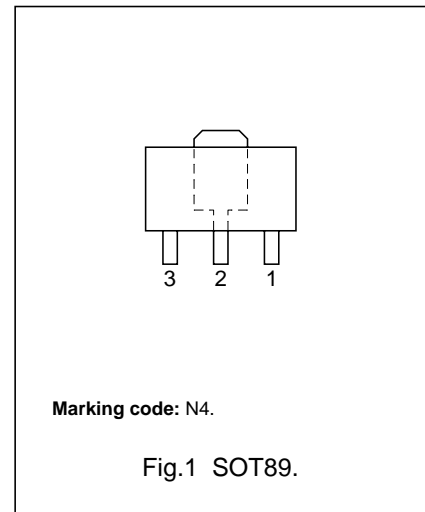
- VHF, UHF and CATV amplifiers.

DESCRIPTION

NPN wideband transistor in a SOT89 plastic package.

PINNING

PIN	DESCRIPTION
1	emitter
2	collector
3	base



QUICK REFERENCE DATA

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	–	15	V
V_{EBO}	collector-base voltage	open collector	–	–	2	V
I_C	collector current (DC)		–	–	120	mA
P_{tot}	total power dissipation	$T_s \leq 60\text{ }^\circ\text{C}$; note 1	–	–	1.2	W
h_{FE}	DC current gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $T_j = 25\text{ }^\circ\text{C}$	100	120	250	
f_T	transition frequency	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 1\text{ GHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	–	9	–	GHz
$ S_{21} ^2$	insertion power gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	12	13	–	dB
F	noise figure	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $\Gamma_S = \Gamma_{opt}$	–	1.9	2.4	dB

Note

1. T_s is the temperature at the soldering point of the collector pin.

NPN wideband transistor

BFQ540

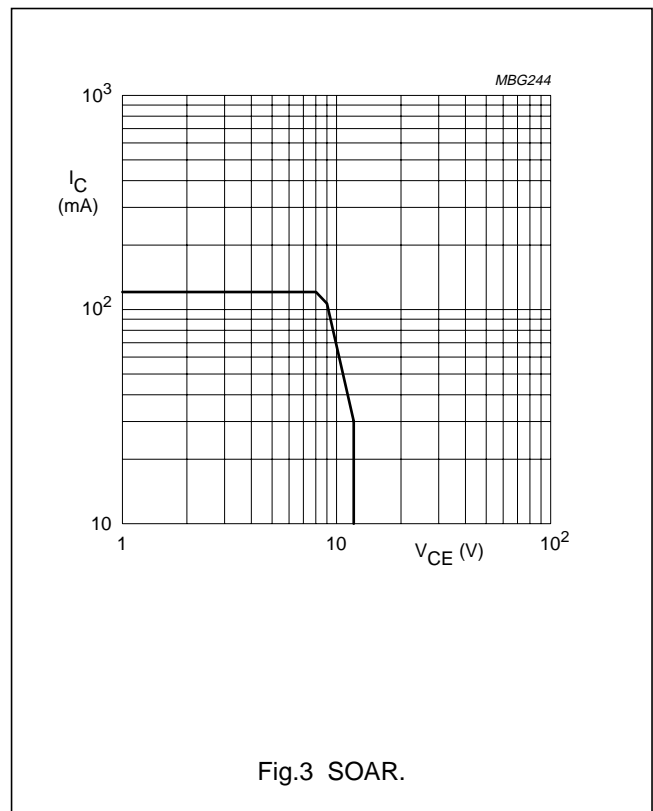
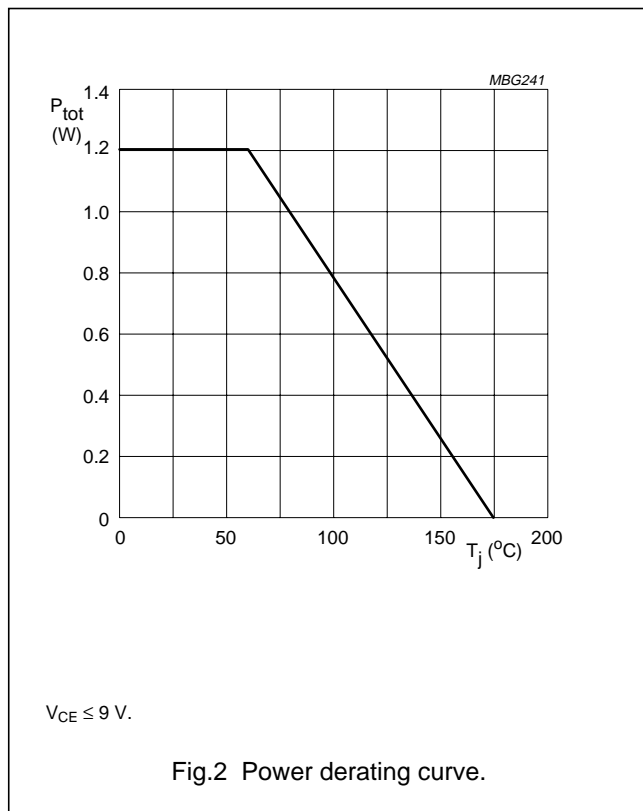
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	20	V
V_{CES}	collector-emitter voltage	$R_{BE} = 0$	–	15	V
V_{EBO}	emitter-base voltage	open collector	–	2	V
I_C	collector current (DC)		–	120	mA
P_{tot}	total power dissipation	$T_s \leq 60\text{ °C}$	–	1.2	W
T_{stg}	storage temperature		–65	+150	°C
T_j	operating junction temperature		–	175	°C

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th\ j-s}$	thermal resistance from junction to soldering point	$T_s \leq 60\text{ °C}; P_{tot} = 1.2\text{ W}$	95	K/W



NPN wideband transistor

BFQ540

CHARACTERISTICS

$T_j = 25\text{ }^\circ\text{C}$ unless otherwise specified.

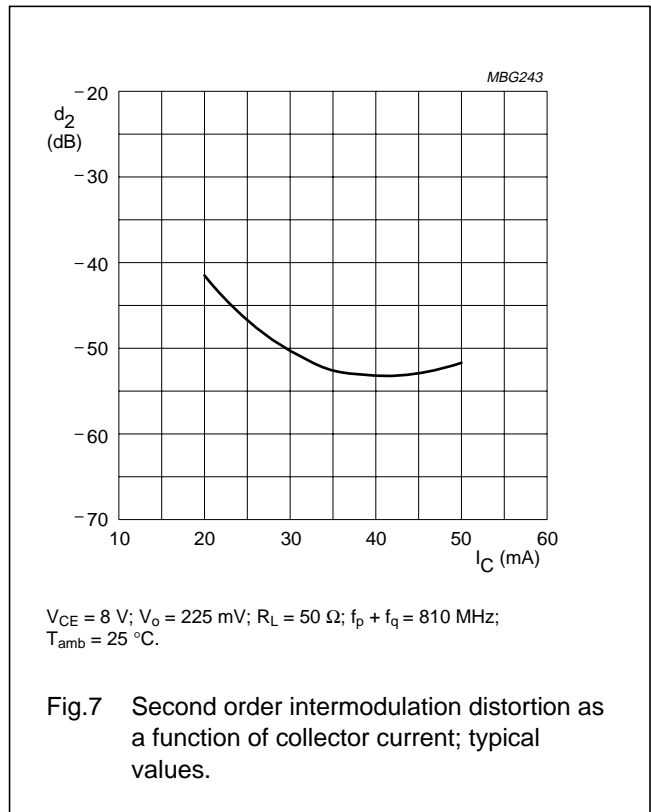
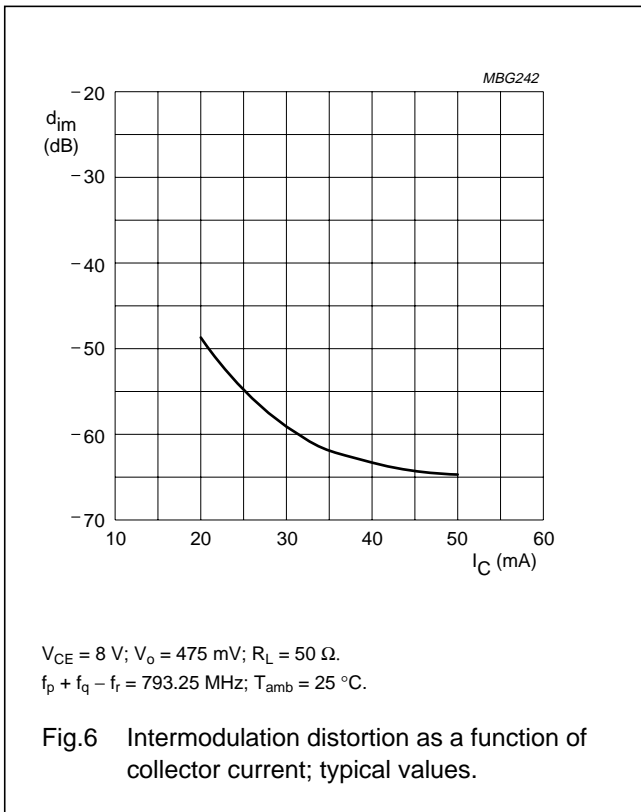
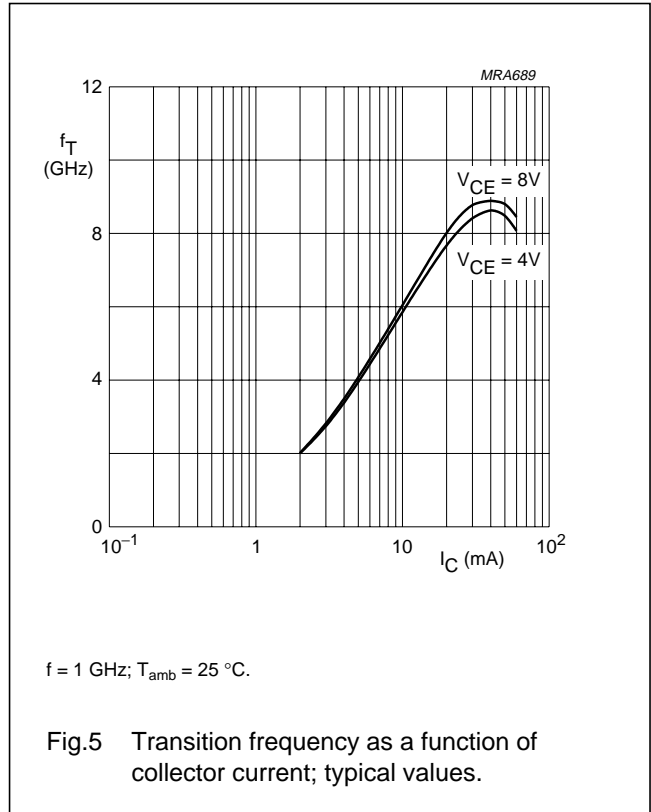
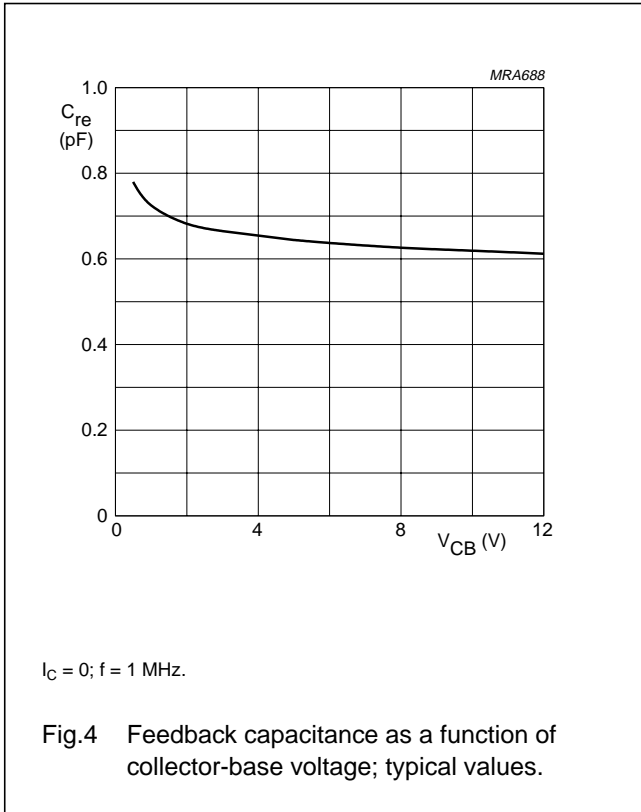
SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
$V_{(BR)CBO}$	collector-base breakdown voltage	open emitter; $I_C = 10\text{ }\mu\text{A}$; $I_E = 0$	20	–	–	V
$V_{(BR)CES}$	collector-emitter breakdown voltage	$R_{BE} = 0$; $I_C = 40\text{ }\mu\text{A}$	15	–	–	V
$V_{(BR)EBO}$	emitter-base breakdown voltage	$I_E = 100\text{ }\mu\text{A}$; $I_C = 0$	2	–	–	V
I_{CBO}	collector-base leakage current	$V_{CB} = 8\text{ V}$; $I_E = 0$	–	–	50	nA
I_{EBO}	emitter-base leakage current	$V_{CB} = 1\text{ V}$; $I_C = 0$	–	–	200	nA
h_{FE}	DC current gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$	100	120	250	
f_T	transition frequency	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f_m = 1\text{ GHz}$	–	9	–	GHz
C_e	emitter capacitance	$I_C = I_e = 0$; $V_{EB} = 0.5\text{ V}$; $f = 1\text{ MHz}$	–	2	–	pF
C_{re}	feedback capacitance	$I_C = 0$; $V_{CE} = 8\text{ V}$; $f = 1\text{ MHz}$	–	0.9	–	pF
$ S_{21} ^2$	insertion power gain	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $T_{amb} = 25\text{ }^\circ\text{C}$	12	13	–	dB
V_o	output voltage	note 1	–	500	–	mV
		note 2	–	350	–	mV
d_2	second order intermodulation distortion	note 3	–	–	–53	dB
F	noise figure	$I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $f = 900\text{ MHz}$; $\Gamma_S = \Gamma_{opt}$	–	1.9	2.4	dB

Notes

- $d_{im} = -60\text{ dB}$ (DIN45004B); $V_{CE} = 8\text{ V}$; $I_C = 40\text{ mA}$; $R_L = 50\text{ }\Omega$;
 $V_p = V_o$; $V_q = V_o - 6\text{ dB}$; $V_r = V_o - 6\text{ dB}$;
 $f_p = 795.25\text{ MHz}$; $f_q = 803.25\text{ MHz}$; $f_r = 805.5\text{ MHz}$;
measured at $f_p + f_q - f_r = 793.25\text{ MHz}$.
- $d_{im} = -60\text{ dB}$ (DIN 45004B); $I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 50\text{ }\Omega$;
 $V_p = V_q = V_o$; $f_p = 806\text{ MHz}$; $f_q = 810\text{ MHz}$;
measured at $2f_p - f_q = 802\text{ MHz}$.
- $I_C = 40\text{ mA}$; $V_{CE} = 8\text{ V}$; $R_L = 50\text{ }\Omega$;
 $V_p = V_q = 225\text{ mV}$; $f_p = 250\text{ MHz}$; $f_q = 560\text{ MHz}$;
measured at $f_p + f_q = 810\text{ MHz}$.

NPN wideband transistor

BFQ540



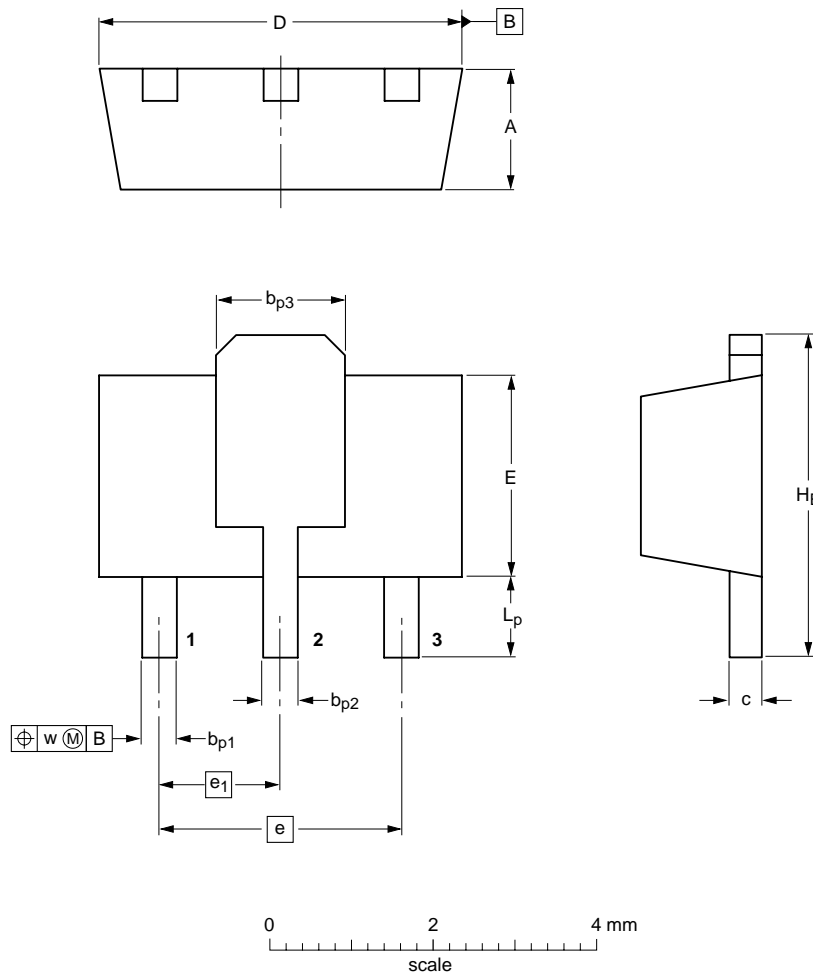
NPN wideband transistor

BFQ540

PACKAGE OUTLINE

Plastic surface-mounted package; collector pad for good heat transfer; 3 leads

SOT89



DIMENSIONS (mm are the original dimensions)

UNIT	A	b_{p1}	b_{p2}	b_{p3}	c	D	E	e	e_1	H_E	L_p	w
mm	1.6	0.48	0.53	1.8	0.44	4.6	2.6	3.0	1.5	4.25	1.2	0.13
	1.4	0.35	0.40	1.4	0.23	4.4	2.4					

OUTLINE VERSION	REFERENCES			EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	JEITA		
SOT89		TO-243	SC-62		06-03-16 06-08-29

Legal information

Data sheet status

Document status ^{[1][2]}	Product status ^[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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Revision history

Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
BFQ540_N_4	20070925	Product data sheet	-	BFQ540_3
Modifications:	• Fig. 1 and package outline updated			
BFQ540_3 (9397 750 07064)	20000523	Product specification	-	BFQ540_2
BFQ540_2 (9397 750 04296)	19980827	Product specification	-	BFQ540_1
BFQ540_1	19950904	Product specification	-	-

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